

UNISONIC TECHNOLOGIES CO., LTD

UT3P06 Preliminary Power MOSFET

3A, 60V (D-S) P-CHANNEL POWER MOSFET

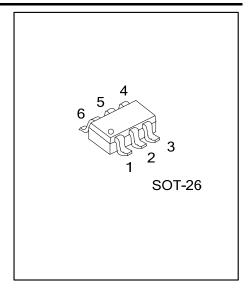
DESCRIPTION

The UTC **UT3P06** is a P-channel enhancement power MOSFET using UTC's advanced technology to provide the customers with perfect $R_{\text{DS(ON)}}$ and low gate charge.

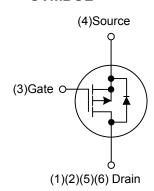
This UTC UT3P06 can be operated with -4.5V low gate voltage.

■ FEATURES

- * $R_{DS(ON)}$ =0.19 Ω @ V_{GS} =-10V, $R_{DS(ON)}$ =0.265 Ω @ V_{GS} =-4.5V
- * Low gate charge (Typically 7nC)



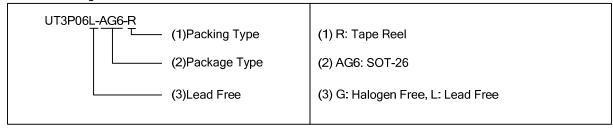
■ SYMBOL



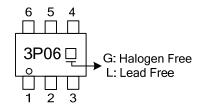
■ ORDERING INFORMATION

Ordering Number		Dealters	Pin Assignment			Da alsia s	
Lead Free	Halogen Free	Package	1, 2, 5, 6	3	4	Packing	
UT3P06L-AG6-R	UT3P06G-AG6-R	SOT-26	D	G	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



MARKING



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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ t DSS}$	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	Ι _D	-3	Α
	Pulsed	I _{DM}	-10	Α
Avalanche Current (L=0.1mH)		I _{AR}	-7	Α
Power Dissipation (Note 1, 2)		P_{D}	3.5	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Surface Mounted on FR4 Board.
- 3. t≤5 sec

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient (Note 1,2)	θ_{JA}	62.5	°C/W	
Junction to Case	θ_{JC}	35	°C/W	

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV_DSS	I _D =-250μA, V _{DS} =0V	-60			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-48V, V _{GS} =0V			-1	μА	
			V _{DS} =-48V, V _{GS} =0V , T _J =150°C			-50		
Gate- Source Leakage Current	Forward	I _{GSS}	V_{GS} =+20V, V_{DS} =0V			+100	nA	
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1			V	
Static Drain-Source On-State Resistance (Note 1)		R _{DS(ON)}	V_{GS} =-10V, I_D =-3A		190	220	mΩ	
			V _{GS} =-4.5V, I _D =-1.9A		265	310		
On State Drain Current (Note 1)		$I_{D(ON)}$	V _{GS} =-10V, V _{DS} =-5V	-10			Α	
SWITCHING PARAMETERS (N	ote 2)							
Total Gate Charge		Q_G			7	14	nC	
Gate to Source Charge		Q_GS	V_{GS} =-10V, V_{DS} =-30V, I_{D} =-3A		1.6		nC	
Gate to Drain Charge		Q_GD			1.2		nC	
Turn-ON Delay Time		$t_{D(ON)}$			8	16	ns	
Rise Time		t_R	V _{DD} =-30V, V _{GEN} =-10V, I _D =-1A,		12	24	ns	
Turn-OFF Delay Time		$t_{D(OFF)}$	R_L =30 Ω , R_G =6 Ω		23	45	ns	
Fall-Time		t_{F}			12	25	ns	
SOURCE- DRAIN DIODE RATIF	NGS AND	CHARACTE	RISTICS (Note 2)					
Maximum Body-Diode Continuous Current		Is				-1.7	Α	
Maximum Body-Diode Pulsed Current		I _{SM}				-10	Α	
Drain-Source Diode Forward Voltage		V_{SD}	I _S =-3A, V _{GS} =0V (Note 1)		-0.8	-1.2	V	

Notes: 1. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%.

2. Guaranteed by design, not subject to production testing.

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